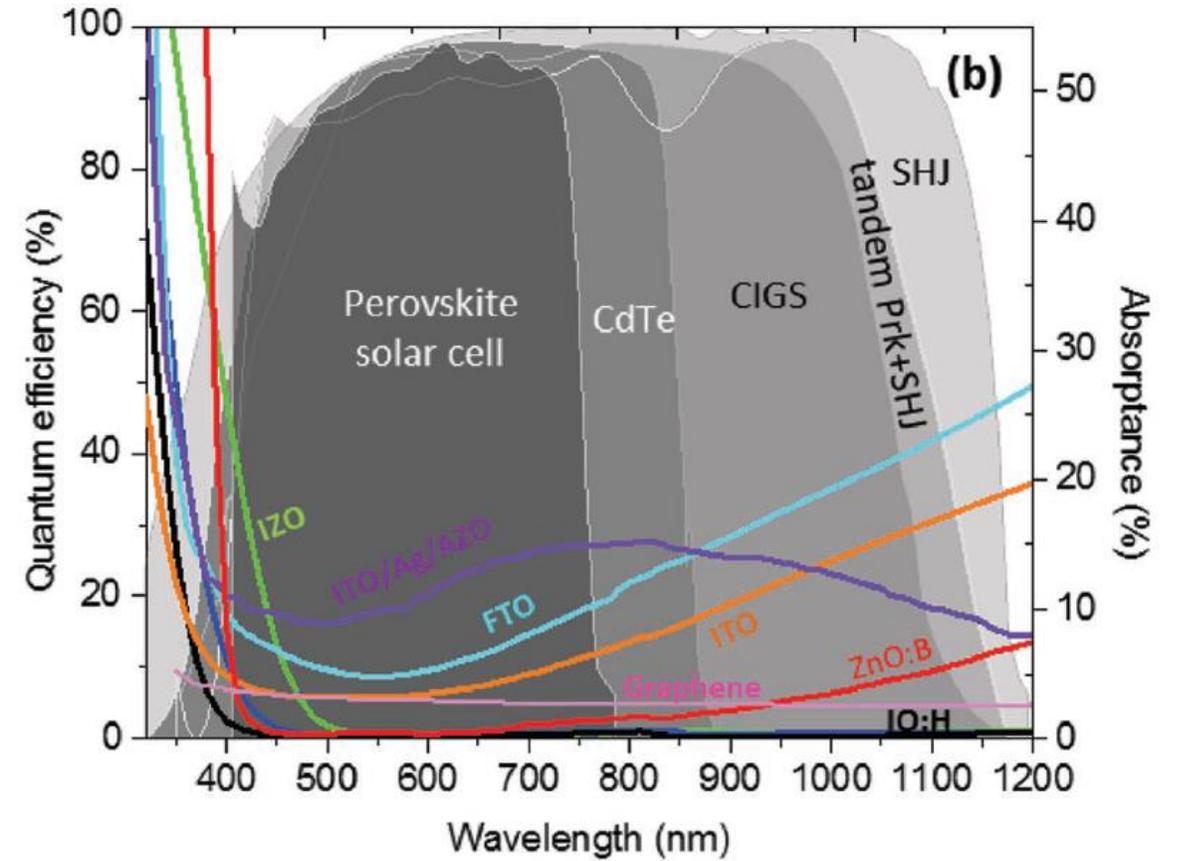
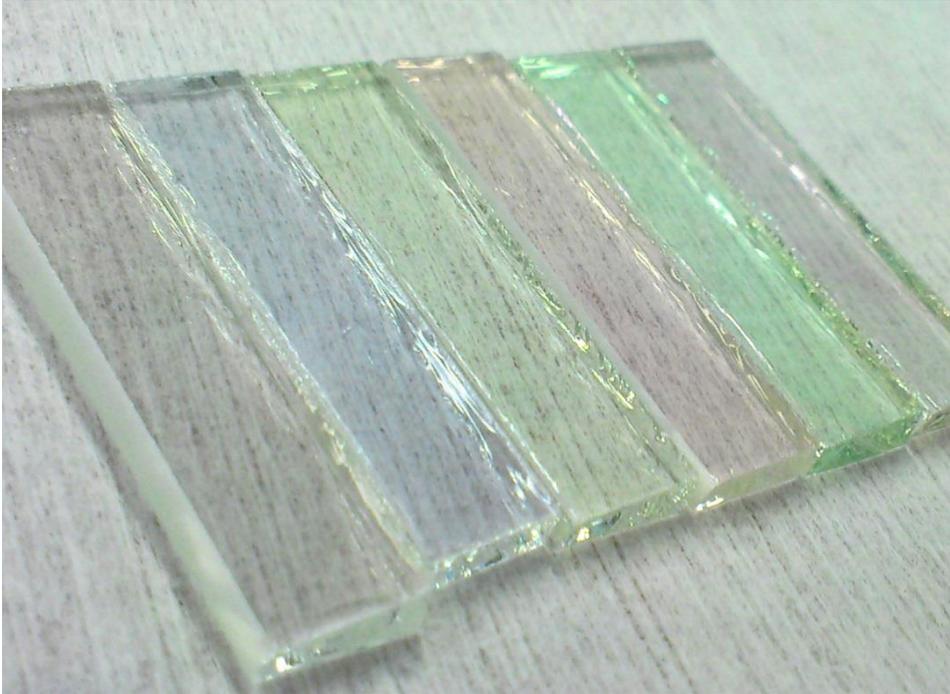


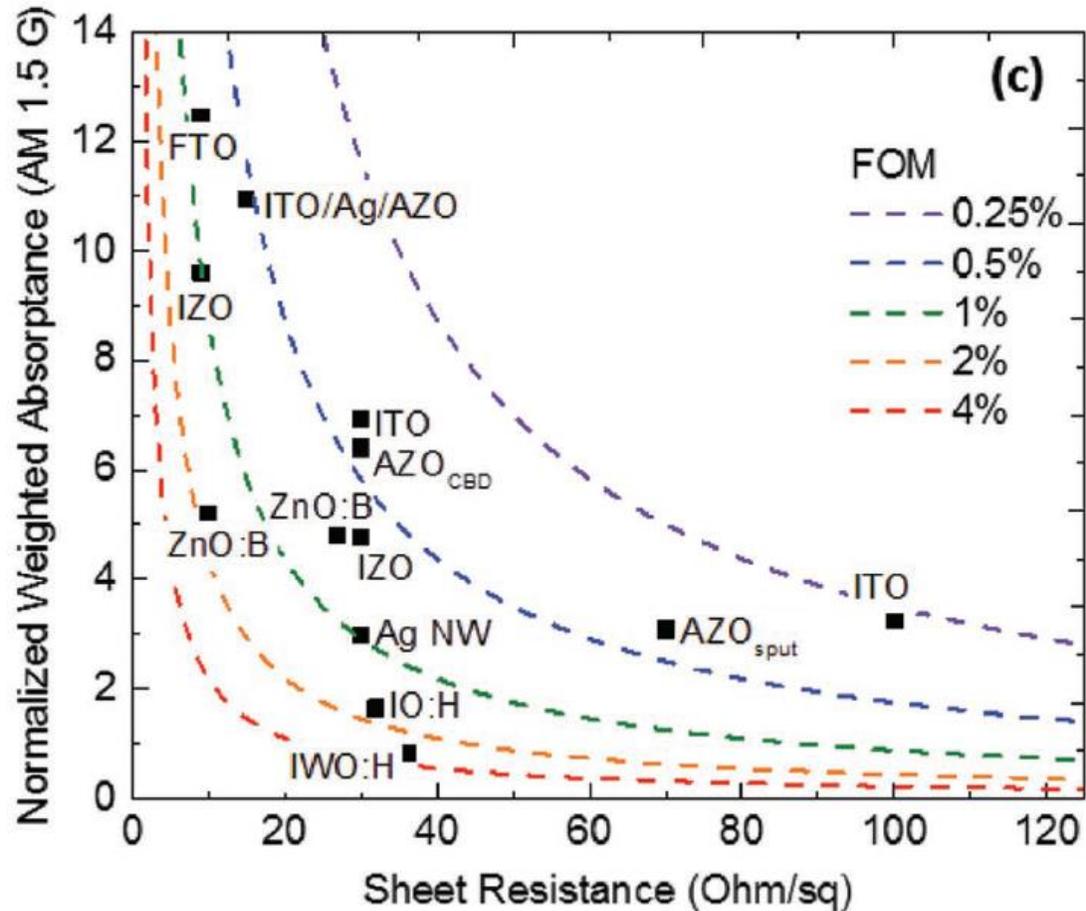
A large, abstract blue graphic on the left side of the slide, consisting of several overlapping, curved shapes in various shades of blue, creating a sense of depth and movement.

Industrielle TCO Schichten für Silizium Solarzellen

Darja Erfurt
28.03.2019

- Einführung
- Kooperation mit Von Ardenne GmbH
- Nationales Projekt DYNASTO





■ Transparent

- im UV, VIS, NIR
- Bandlücke $E_g > 3$ eV

■ Leitfähig

- Spez. Leitfähigkeit $\sigma > 10^3 \Omega^{-1}\text{cm}^{-1}$
- Spez. Widerstand $\rho < 10^{-3} \Omega\text{cm}$

$$\sigma = \frac{1}{\rho} = n_e \mu_e e$$

n_e ... Ladungsträgerdichte
 μ_e ... Ladungsträgerbeweglichkeit
 e ... Elementarladung

$$R_{Sq} = \frac{\rho}{d}$$

R_{Sq} ... Schichtwiderstand
 d ... Schichtdicke

■ Typische TCOs

- ZnO:Al (AZO)
- In_2O_3 :Sn (ITO)
- SnO_2 :F (FTO)

Lab Line @ HZB

PVcomB



Wet Chemistry



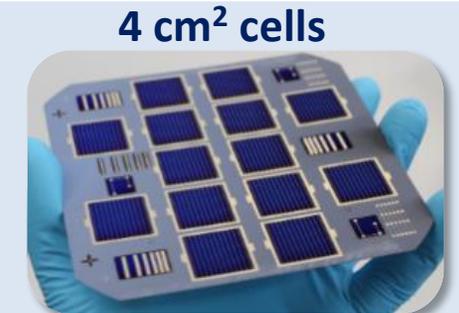
AMAT AKT1600
PECVD



Leybold Optics A600V7
Sputtering

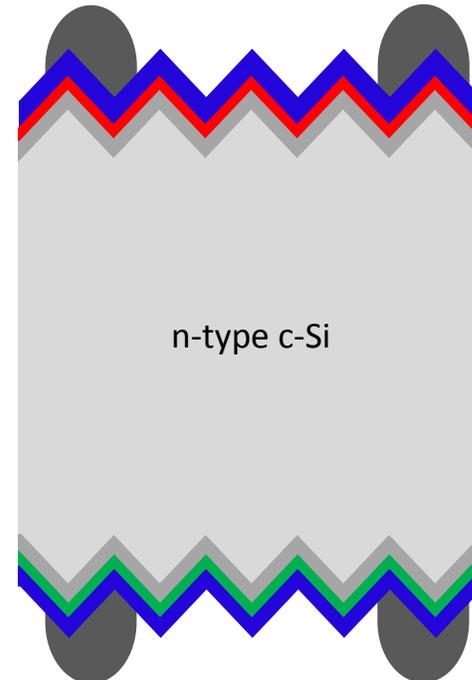
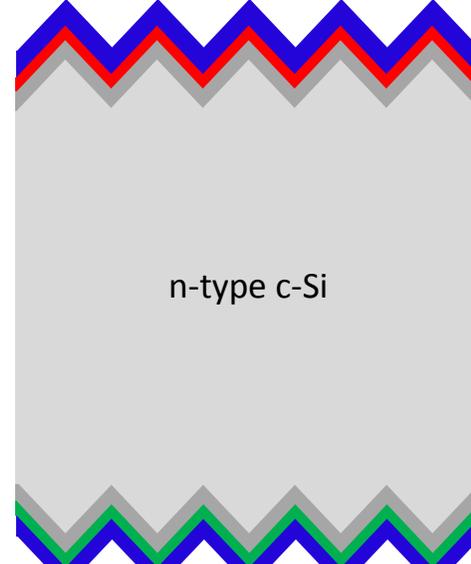
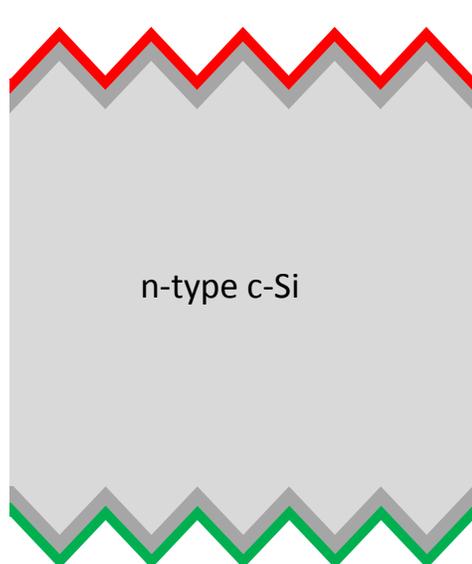
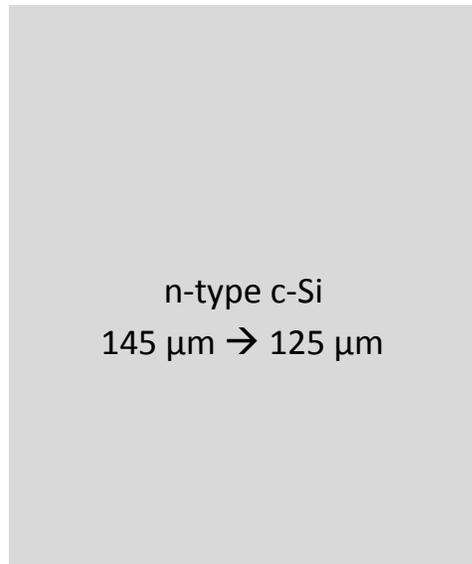


Screen Printing



4 cm² cells

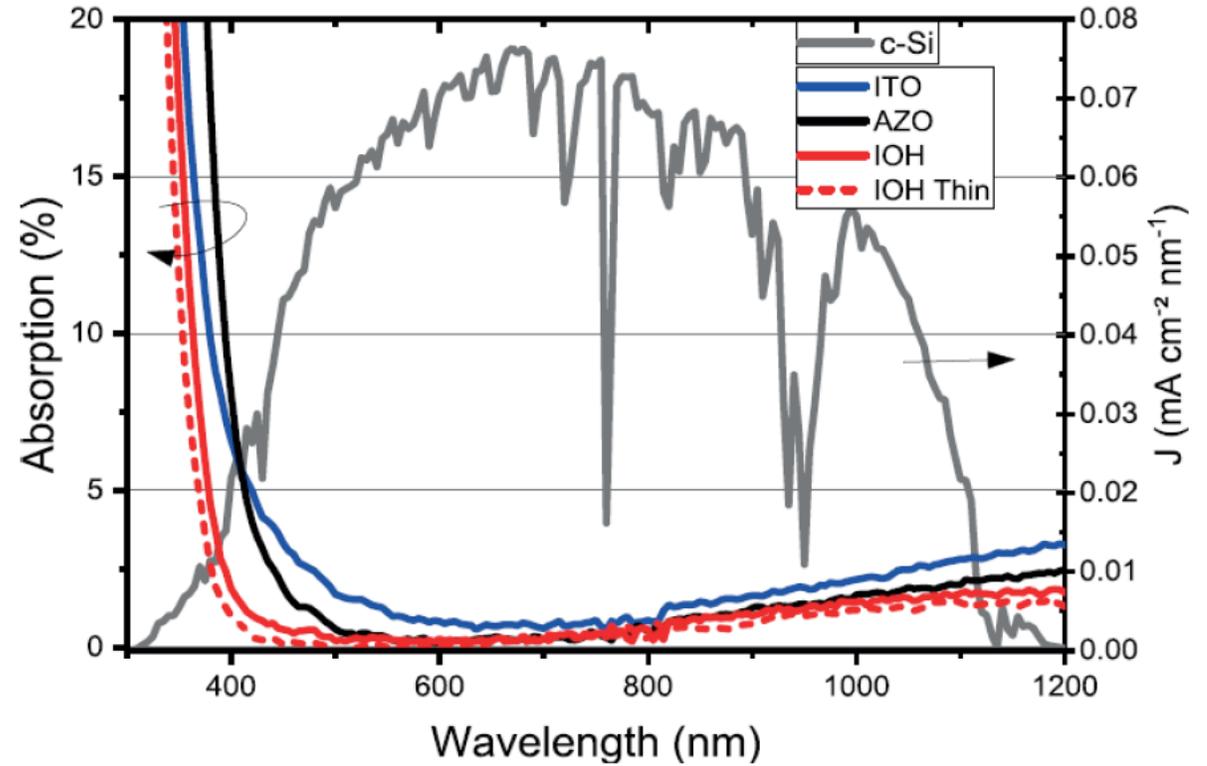
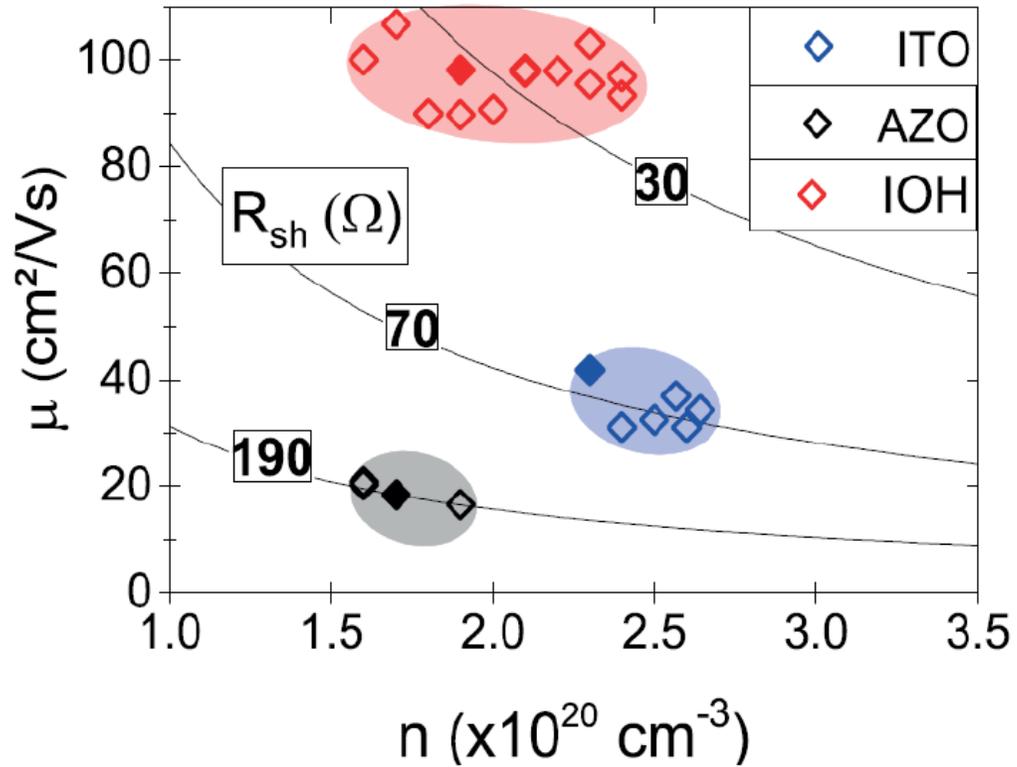
$\eta = 23,5\%$, certified



Ag grid

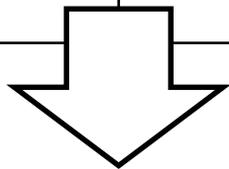
TCO front ~ 75 nm
(n) nc-Si:H 12 nm
(i) a-Si:H < 5 nm

(i) a-Si:H < 5 nm
(p) a-Si:H < 8 nm
TCO rear ~ 75 nm

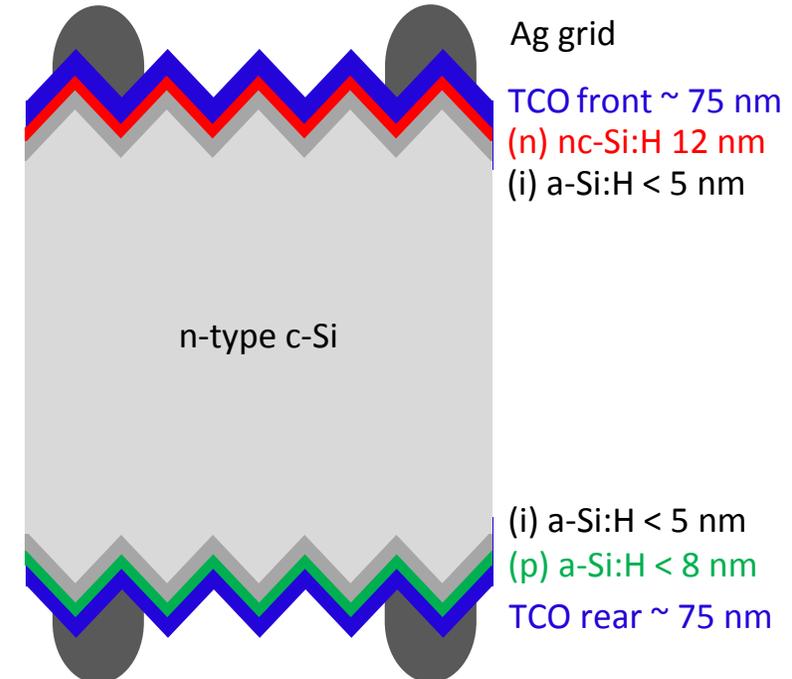
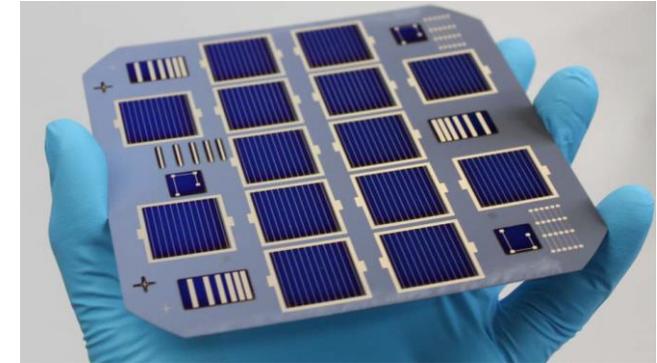


- Anwendung als Front-TCO in SHJ-Solarzelle
- Zudem Simulation der Ergebnisse

<p>HZB</p>	<ul style="list-style-type: none"> ▪ Bereitstellen von SHJ Solarzellen (ohne Front-TCO und Ag-Grid) ▪ Herstellen von SHJ Referenz Solarzellen
<p>Von Ardenne</p>	<ul style="list-style-type: none"> ▪ Test verschiedener TCO Schichten als Front-TCO <ul style="list-style-type: none"> ▪ Hohe Abscheiderate, $T > 100^{\circ}\text{C}$ ▪ In_2O_3 Dopingvariationen: ITO, ITiO, Y (IO:X)
<p>HZB</p>	<ul style="list-style-type: none"> ▪ Fertigstellung und Analyse der Solarzellen



Evaluierung der Solarzellen Parameter in Abhängigkeit des Front-TCOs von Von Ardenne



35th European Photovoltaic Solar Energy Conference and Exhibition

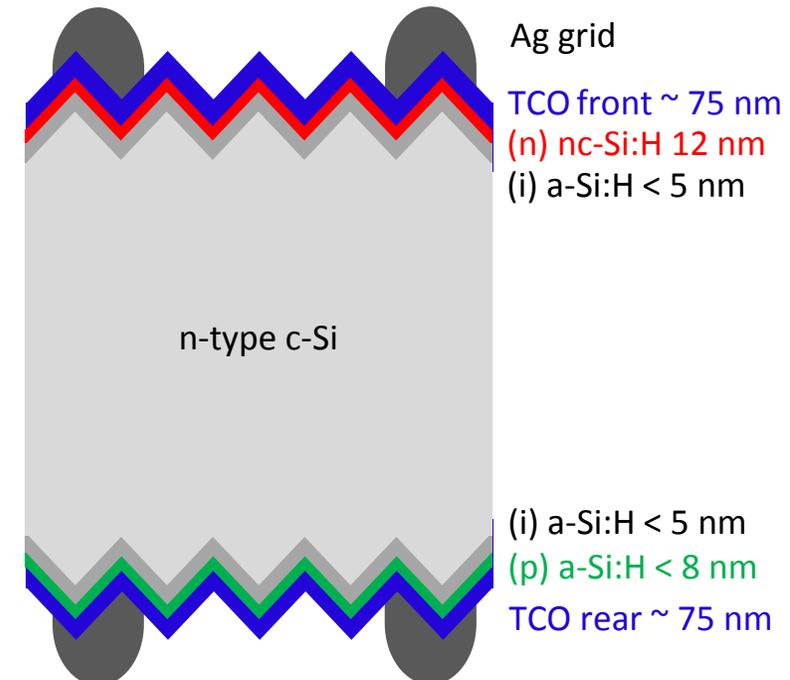
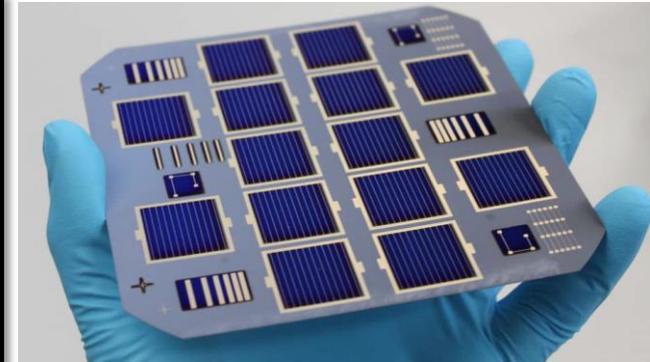
HIGH MOBILITY TRANSPARENT CONDUCTIVE OXIDES FOR SILICON HETEROJUNCTION SOLAR CELLS DEPOSITED BY ROTATABLE MAGNETRONS

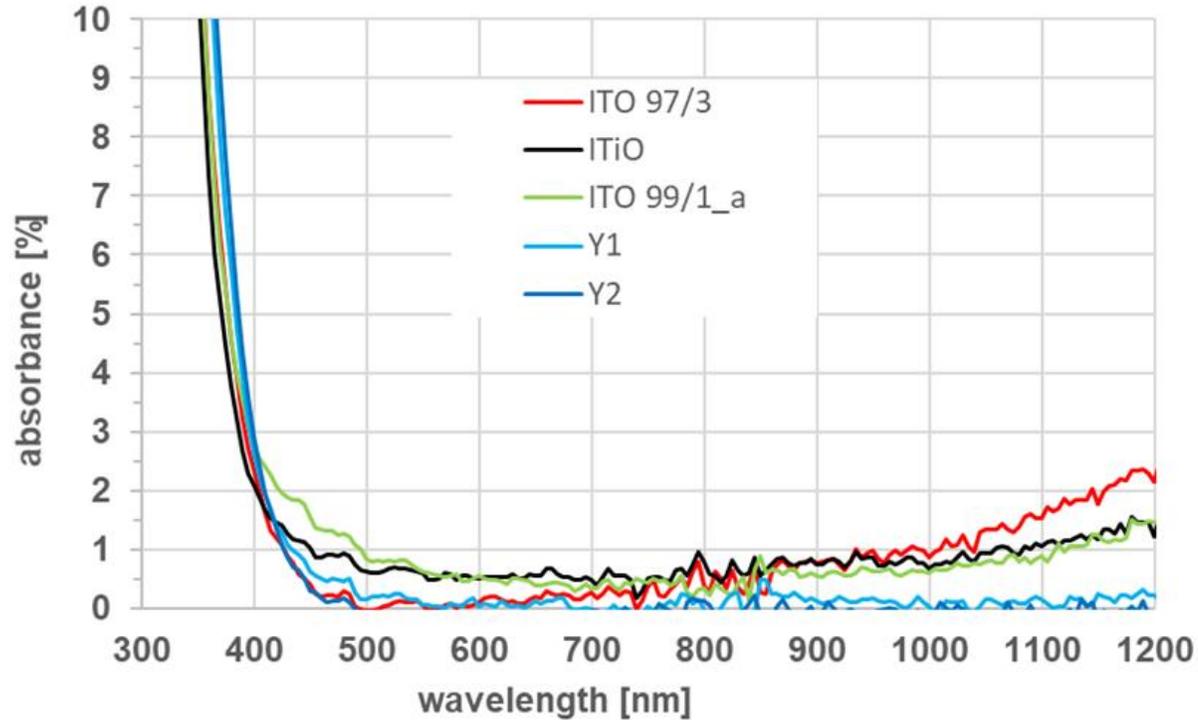
M. Dimer¹, A. Cruz², Er-Chien Wang², A.B. Morales-Vilches², J. Löhnert¹,
U. Graupner¹, M. Thumsch¹, B. Stannowski², E. Schneiderlöchner¹

¹VON ARDENNE GmbH, Am Hahnweg 8, 01328 Dresden, Germany.

²Helmholtz-Zentrum Berlin, PVcomB, Schwarzschildstr. 3, 12489 Berlin, Germany.

ABSTRACT: Sputtered indium tin oxide (ITO) is a widespread used material for application as transparent conducting oxide as the front contact of rear-junction silicon heterojunction solar cells. Standard ITO films suffer from too high parasitic absorption in both the short- and the long-wavelength range. The aim of this contribution is to investigate lower absorbing TCOs deposited with industrial DC sputtering from rotatable targets. High V_{oc} values >735 mV demonstrate that in spite of the high-power industrial DC sputter process no significant sputter damage is observed, independent of the target material. Cell efficiencies up to 23.3% are obtained with titanium-doped (ITiO) and tin-doped indium oxide (ITO 99/1). The highest short circuit current values of 39.6 mA/cm² are reached with an ultimately low-carrier and high-mobility indium-oxide-based material. The cell efficiency in this case, however, is over-compensated by a too low FF, mostly due to a higher contact resistivity and TCO sheet resistances. We ascribe this effect to the very low carrier concentration.





	ITO 97/3	ITiO	ITO 99/1	Y1	Y2
μ_{Hall} (cm^2/Vs)	57 (57)	76 (79)	65 (69)	84 (89)	79 (79)
N_e ($1\text{E}20 \text{ cm}^{-3}$)	2.7 (2.7)	2.2 (2.0)	1.8 (1.8)	1.3 (0.9)	1.1 (0.7)
R_{sheet} (Ω)	41 (42)	34 (36)	47 (45)	51 (71)	68 (136)

In Klammern: Nach Tempervorgang: 200°C, 30 min

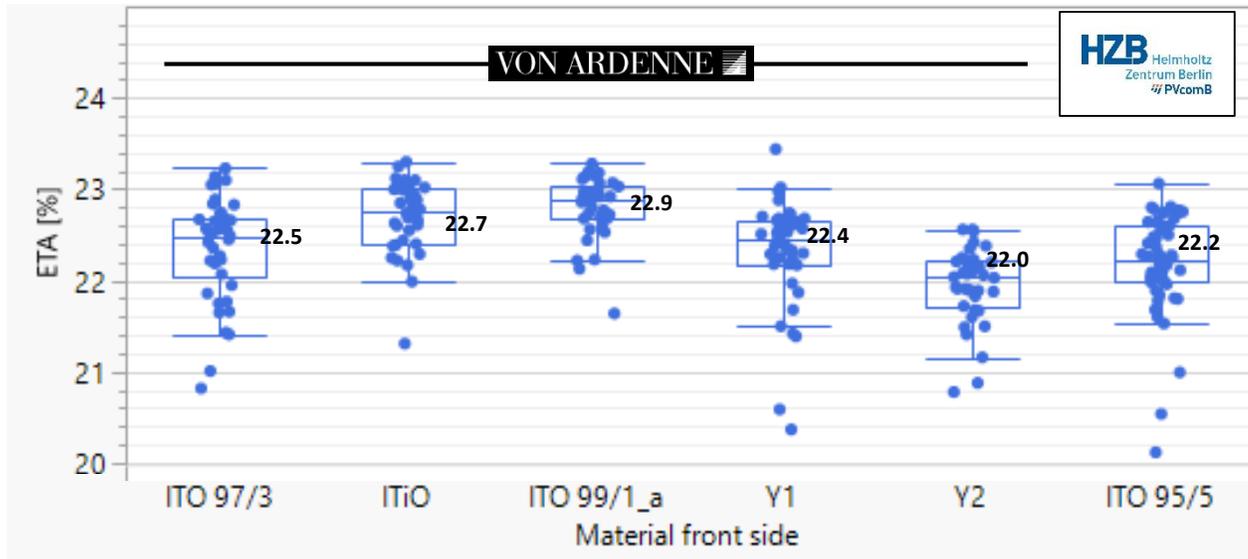
Abscheidung:



Rotatable Targets

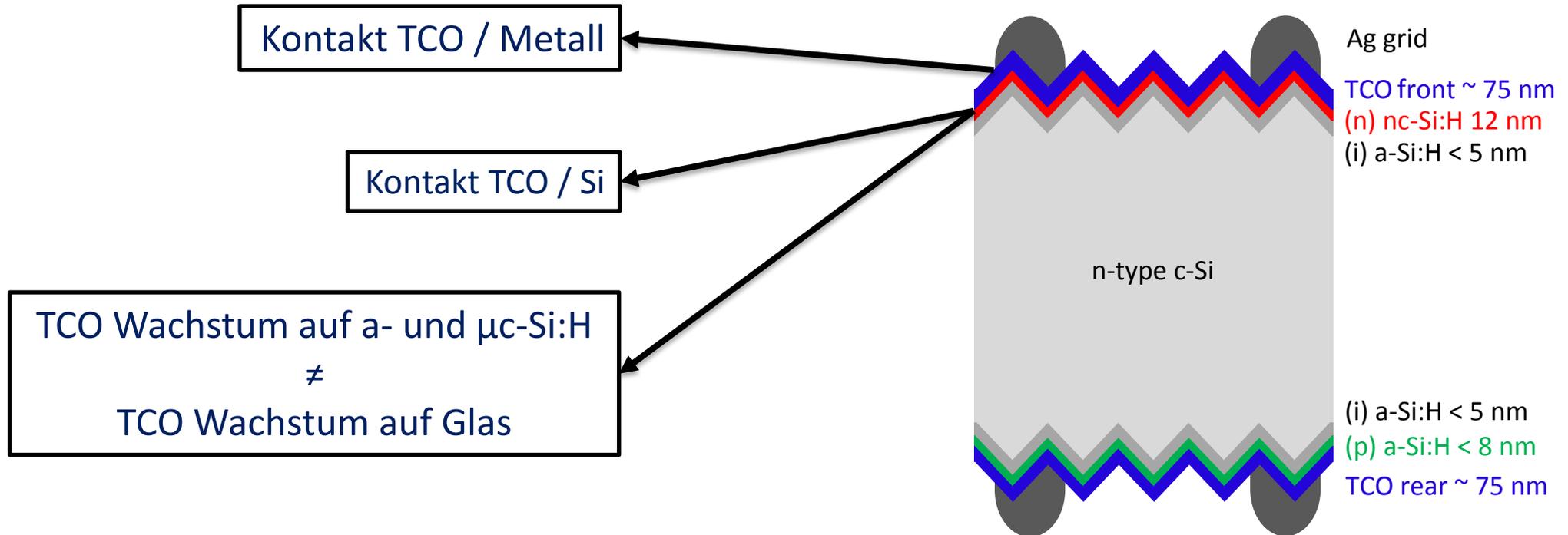
Analyse der TCO Schichten
auf Glas

M. Dimer *et al.*, presented at EU-PVSEC Brussels 2018.



- ITiO und ITO 99/1
 - höchste Effizienz und Füll Faktor
- Alle Materialien
 - $V_{OC} \sim 735 - 740$ mV
 - Keine Schäden durchs Sputtern
- In_xO_y basierte Materialien Y1, Y2
 - Höchste J_{SC} Werte
 - Geringer Füll Faktor
 - TCO / Si Kontaktprobleme

M. Dimer *et al.*, presented at EU-PVSEC Brussels 2018.



Gefördert durch:



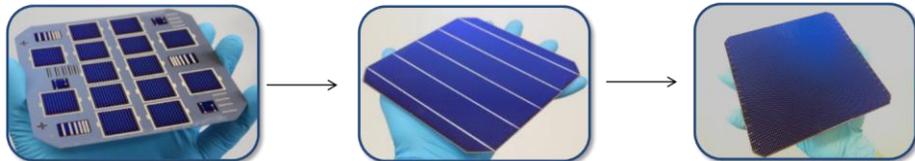
aufgrund eines Beschlusses
des Deutschen Bundestages

Teilvorhaben: Entwicklung des vorderseitigen Kontaktsystems



VON ARDENNE 

- Entwicklung kostengünstiger & stabiler TCOs für Hoch-Effizienz SHJ Solarzellen
- 6" SHJ Solarzellen mit 24 % Wirkungsgrad



- Modulfertigung und Langzeitstabilitäts-Tests

- Massenfertigungstaugliche in-line Charakterisierungsmethode für TCO (auf texturiertem Wafer)



- Industrielle Prozessentwicklung
 - TCO Abscheidung auf bis zu 30 x 60 cm² möglich
 - Verschiedene TCOs verfügbar (ITO, IOH, ZnO, ...)
 - SHJ Solarzellen auf bis zu 6 Zoll Wafern möglich

- PVcomB als Kooperationspartner
 - Langjährige Erfahrung in Zusammenarbeit mit industriellen Partnern und Instituten
 - Bereitstellung und Charakterisierung von Proben
 - Beratende Funktion



Technologietransfer von der akademischen Forschung zu industriell kompatiblen, relevanten und tragfähigen Technologien !

Vielen Dank für die Aufmerksamkeit!